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## 270 nm Pseudomorphic Ultraviolet Light-Emitting Diodes with Over 60 mW Continuous Wave Output Power

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#	Paper	IF	Citations
148	Enhancement of light extraction efficiency in sub-300nm nitride thin-film flip-chip light-emitting diodes. <b>2013</b> , 89, 156-160		16
147	Plasma-assisted molecular beam epitaxy of Al(Ga)N layers and quantum well structures for optically pumped mid-UV lasers on c-Al <sub>2</sub> O <sub>3</sub> . <i>Semiconductor Science and Technology</i> , <b>2014</b> , 29, 084008	1.8	35
146	Hexagonal boron nitride for deep ultraviolet photonic devices. <i>Semiconductor Science and Technology</i> , <b>2014</b> , 29, 084003	1.8	93
145	AlGa <sub>N</sub> /Ga <sub>N</sub> Nanostructures for UV Light Emitting Diodes. <b>2014</b> ,		1
144	Composition dependent valence band order in c-oriented wurtzite AlGa <sub>N</sub> layers. <b>2014</b> , 116, 113506		20
143	Deep-ultraviolet light emission properties of nonpolar M-plane AlGa <sub>N</sub> quantum wells. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 053104	3.4	30
142	High-power pseudomorphic mid-ultraviolet light-emitting diodes with improved efficiency and lifetime. <b>2014</b> ,		4
141	Recent progress and future prospects of AlGa <sub>N</sub> -based high-efficiency deep-ultraviolet light-emitting diodes. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 100209	1.4	376
140	High-output-power 255/280/310 nm deep ultraviolet light-emitting diodes and their lifetime characteristics. <i>Semiconductor Science and Technology</i> , <b>2014</b> , 29, 084005	1.8	67
139	Bulk AlN growth by physical vapour transport. <i>Semiconductor Science and Technology</i> , <b>2014</b> , 29, 084002	1.8	54
138	Low dislocation density AlGa <sub>N</sub> epilayers by epitaxial overgrowth of patterned templates. <i>Journal of Crystal Growth</i> , <b>2014</b> , 388, 76-82	1.6	16
137	Optically-pumped 285 nm edge stimulated emission from AlGa <sub>N</sub> -based LED structures grown by MOCVD on sapphire substrates. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 112101	1.4	6
136	Photovoltaic powered ultraviolet and visible light-emitting diodes for sustainable point-of-use disinfection of drinking waters. <b>2014</b> , 493, 185-96		60
135	Hydride vapor phase epitaxy of AlN using a high temperature hot-wall reactor. <i>Journal of Crystal Growth</i> , <b>2014</b> , 403, 29-31	1.6	14
134	Deep ultraviolet photopumped stimulated emission from partially relaxed AlGa <sub>N</sub> multiple quantum well heterostructures grown on sapphire substrates. <b>2014</b> , 32, 061204		10
133	. <b>2014</b> ,		2
132	Quasi-pseudomorphic AlGa <sub>N</sub> based deep ultraviolet LEDs over sapphire substrates. <b>2015</b> ,		1

131	Environmentally friendly method to grow wide-bandgap semiconductor aluminum nitride crystals: Elementary source vapor phase epitaxy. <b>2015</b> , 5, 17405		25
130	A 350-nm-band GaN/AlGaN multiple-quantum-well laser diode on bulk GaN. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 151103	3.4	32
129	Substrates and epitaxial deposition processes for Group III-nitride thin films and power device heterostructures. <b>2015</b> , 40, 406-411		0
128	Optimization of p-electrode pattern for AlGaN-based deep-ultraviolet light-emitting diodes. <b>2015</b> ,		
127	AlGaN devices and growth of device structures. <b>2015</b> , 50, 3267-3307		37
126	Progress of high-power deep-ultraviolet LEDs. <b>2015</b> ,		5
125	Light extraction enhancement of 265 nm deep-ultraviolet light-emitting diodes with over 90 mW output power via an AlN hybrid nanostructure. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 131104	3.4	122
124	E-beam pumped mid-UV sources based on MBE-grown AlGaN MQW. <b>2015</b> , 212, 1011-1016		24
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120	Dominance of radiative recombination from electron-beam-pumped deep-UV AlGaN multi-quantum-well heterostructures. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 181105	3.4	28
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118	Preparation of deep UV transparent AlN substrates with high structural perfection for optoelectronic devices. <b>2016</b> , 18, 3488-3497		47
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106	Ultrathin GaN quantum disk nanowire LEDs with sub-250 nm electroluminescence. <b>2016</b> , 8, 8024-32		36
105	An AlGaIn Core-Shell Tunnel Junction Nanowire Light-Emitting Diode Operating in the Ultraviolet-C Band. <b>2017</b> , 17, 1212-1218		94
104	LED revolution: fundamentals and prospects for UV disinfection applications. <b>2017</b> , 3, 188-202		132
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100	Development of a method for the characterization and operation of UV-LED for water treatment. <b>2017</b> , 122, 570-579		49
99	Uneven AlGaIn multiple quantum well for deep-ultraviolet LEDs grown on macrosteps and impact on electroluminescence spectral output. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 061002	1.4	41
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97	Polarization Effect in AlGaIn-Based Deep-Ultraviolet Light-Emitting Diodes. <i>IEEE Journal of Quantum Electronics</i> , <b>2017</b> , 53, 1-6	2	16
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